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**AMENDMENTS TO THE CLAIMS:**

Without prejudice, this listing of the claims replaces all prior versions and listings of the claims in the present application:

**LISTING OF CLAIMS:**

1-14 (Canceled).

15. (Currently Amended) The method according to claim [[14]] 19, wherein the dividing step includes the sub-steps of:

applying a nitride layer; and

structuring the nitride layer using a photoresist technique, wherein the positive areas of the surface of the wafer are defined by a part of the surface covered with the nitride layer.

16. (Previously Presented) The method according to claim 15, further comprising the step of removing the nitride layer at least in subareas of the positive areas after the negative areas are provided with the first passivation layer and before the wafer is etched.

17. (Previously Presented) The method according to claim 15, wherein the structuring step includes a step of removing a photoresist at at least one of the edge areas after exposing the photoresist.

18. (Previously Presented) The method according to claim 17, wherein the photoresist is removed after exposing and developing the photoresist.

19. (Currently Amended) ~~The method according to claim 20, further comprising the step of~~  
A method of etching a wafer, comprising the steps of:

providing a wafer having a surface and edge areas;